

Dual N-Channel Enhancement Mode MOSFET

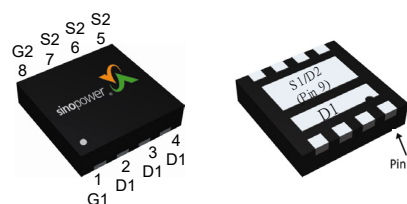
Features

- Channel 1**
 30V/14A*
 $R_{DS(ON)} = 8.5\text{m}\Omega(\text{max.}) @ V_{GS} = 10\text{V}$
 $R_{DS(ON)} = 11.9\text{m}\Omega(\text{max.}) @ V_{GS} = 4.5\text{V}$
- Channel 2**
 30V/24A*
 $R_{DS(ON)} = 4.7\text{m}\Omega(\text{max.}) @ V_{GS} = 10\text{V}$
 $R_{DS(ON)} = 7\text{m}\Omega(\text{max.}) @ V_{GS} = 4.5\text{V}$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

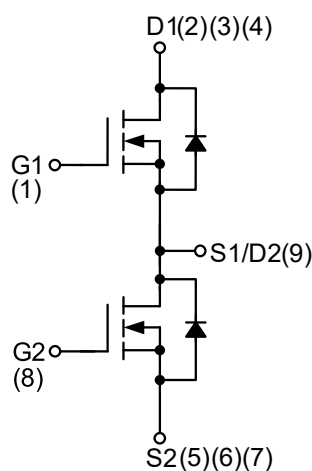
Applications

- Synchronous Buck Converters.
- High Current, Low Duty Cycle Applications.
- Multiphase Synchronous Buck Converters.
- POL DC-DC Converters.

Pin Description



DFN3x3E-8_EP2



N-Channel MOSFET

Ordering and Marking Information

SM3385EQ □□□-□□□ Assembly Material Handling Code Temperature Range Package Code	Package Code QG : DFN3x3E-8_EP2 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM3385EQ QG : SM 3385EQ XXXXX ● 	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Channel 1	Channel 2	Unit
Common Ratings					
V _{DSS}	Drain-Source Voltage		30	30	V
V _{GSS}	Gate-Source Voltage		±20	±20	
T _J	Maximum Junction Temperature		150		°C
T _{STG}	Storage Temperature Range		-55 to 150		
I _S	Diode Continuous Forward Current	T _C =25°C	14*	24*	A
I _D	Continuous Drain Current	T _C =25°C	14*	24*	A
		T _C =100°C	14*	24*	
I _{DM} ^a	Pulse Drain Current Tested	T _C =25°C	56	96	A
P _D	Maximum Power Dissipation	T _C =25°C	28	42	W
		T _C =100°C	11	17	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	4.5	3	°C/W
I _D	Continuous Drain Current	T _A =25°C	11	15	A
		T _A =70°C	9	12	
I _{DM} ^a	Pulse Drain Current Tested	T _A =25°C	45	59	A
P _D	Maximum Power Dissipation	T _A =25°C	1.6	1.6	W
		T _A =70°C	1	1	
R _{θJA} ^b	Thermal Resistance-Junction to Ambient	t ≤ 10s	42	42	°C/W
		Steady State	80	80	
I _{AS} ^c	Avalanche Current, Single pulse	L=0.1mH	19	23	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.1mH	18	26.5	mJ

Note * : Maximum continuous current is limited by bonding wire.

Note a : Pulse width limited by maximum junction temperature.

Note b : Surface mounted on 1in^2 pad area, steady state $t = 999\text{s}$.

Note c : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Channel 1			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	1.6	2.2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =7A	-	6.8	8.5	mΩ
		T _J =125°C	-	9.7	-	
		V _{GS} =4.5V, I _{DS} =4A	-	8.8	11.9	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =4A	-	7.6	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =3.5A, V _{GS} =0V	-	0.75	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =7A, dI _{SD} /dt=100A/μs	-	19.3	-	ns
t _a	Charge Time		-	8.3	-	
t _b	Discharge Time		-	11	-	
Q _{rr}	Reverse Recovery Charge		-	8.4	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	800	1040	pF
C _{oss}	Output Capacitance		-	313	-	
C _{rss}	Reverse Transfer Capacitance		-	32	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	11	20	ns
t _r	Turn-on Rise Time		-	9	17	
t _{d(OFF)}	Turn-off Delay Time		-	23	42	
t _f	Turn-off Fall Time		-	18	33	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =7A	-	11.7	17.6	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =7A	-	5.8	8.7	
Q _{gth}	Threshold Gate Charge		-	1.3	-	
Q _{gs}	Gate-Source Charge		-	1.9	-	
Q _{gd}	Gate-Drain Charge		-	1.5	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

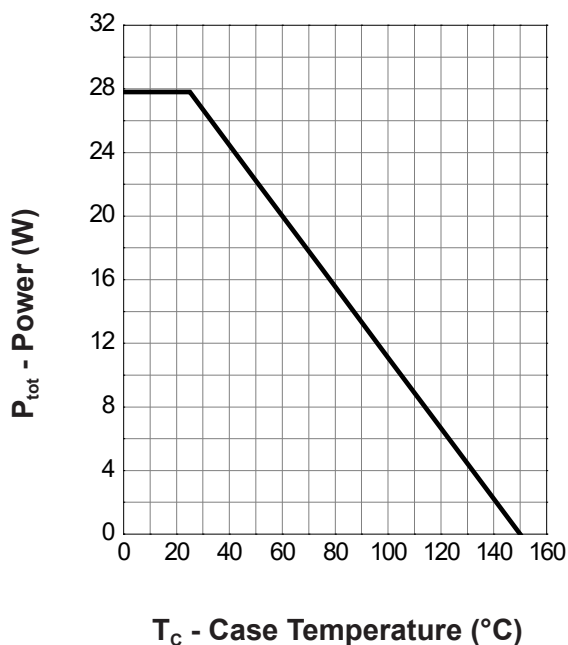
Symbol	Parameter	Test Conditions	Channel 2			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	1.6	2.2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =12A	-	3.9	4.7	mΩ
		T _J =125°C	-	5.5	-	
		V _{GS} =4.5V, I _{DS} =7A	-	5.4	7	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =7A	-	15	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =6A, V _{GS} =0V	-	0.75	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =12A, dI _{SD} /dt=100A/μs	-	25.5	-	ns
t _a	Charge Time		-	10	-	
t _b	Discharge Time		-	15.5	-	
Q _{rr}	Reverse Recovery Charge		-	11.6	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	1075	1398	pF
C _{oss}	Output Capacitance		-	400	-	
C _{rss}	Reverse Transfer Capacitance		-	45	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	12	22	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	25.5	46	
t _f	Turn-off Fall Time		-	25	45	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =12A	-	15.5	23.3	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =12A	-	7.8	11.7	
Q _{gth}	Threshold Gate Charge		-	1.7	-	
Q _{gs}	Gate-Source Charge		-	2.6	-	
Q _{gd}	Gate-Drain Charge		-	2.2	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

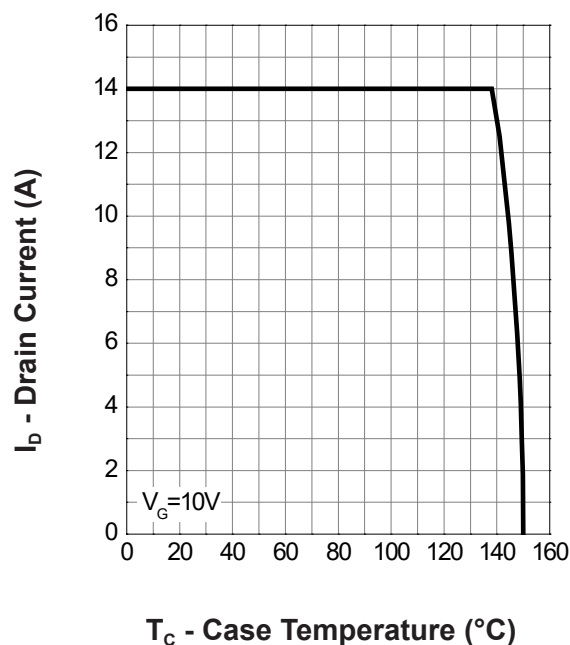
Note e : Guaranteed by design, not subject to production testing.

Channel 1 Typical Operating Characteristics

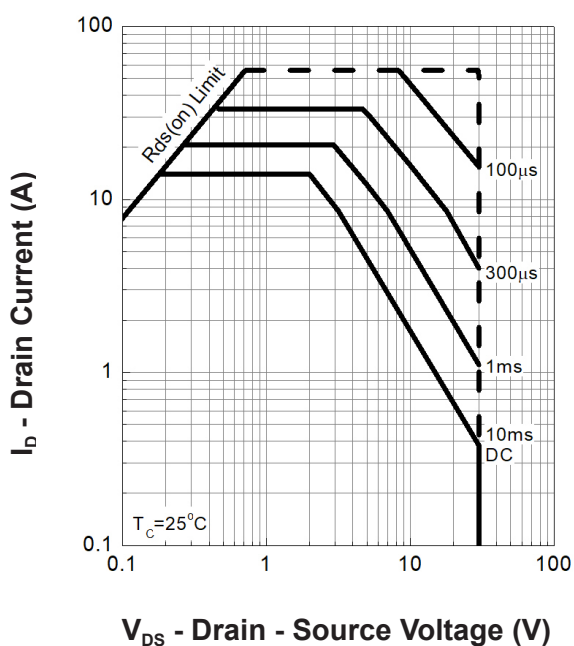
Power Dissipation



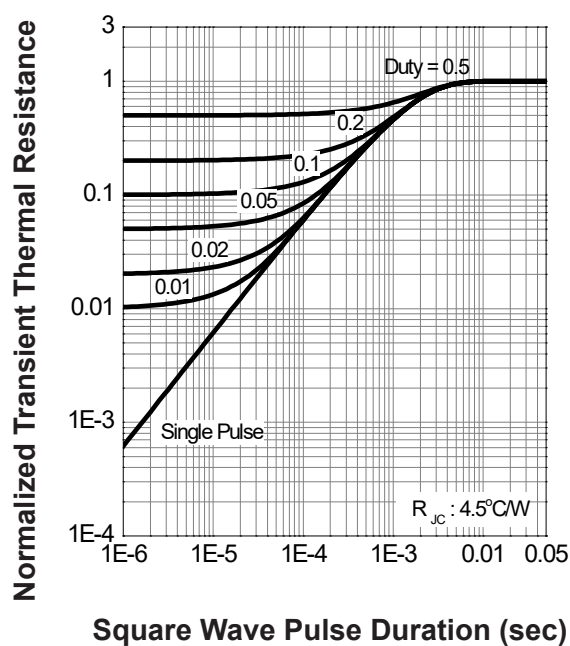
Drain Current



Safe Operation Area

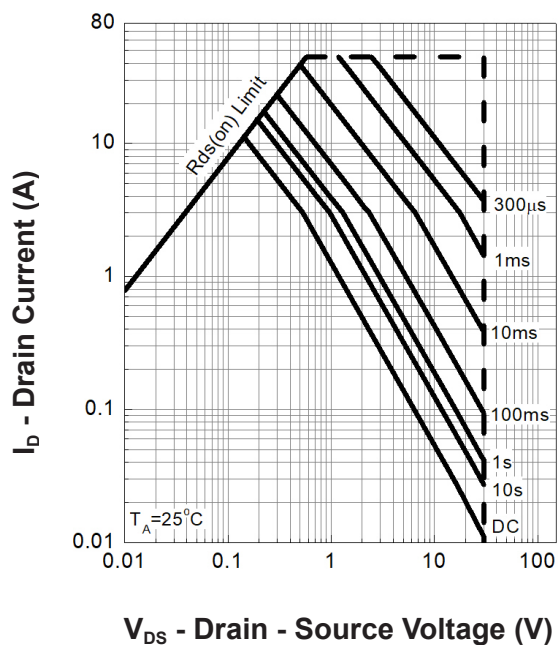


Thermal Transient Impedance

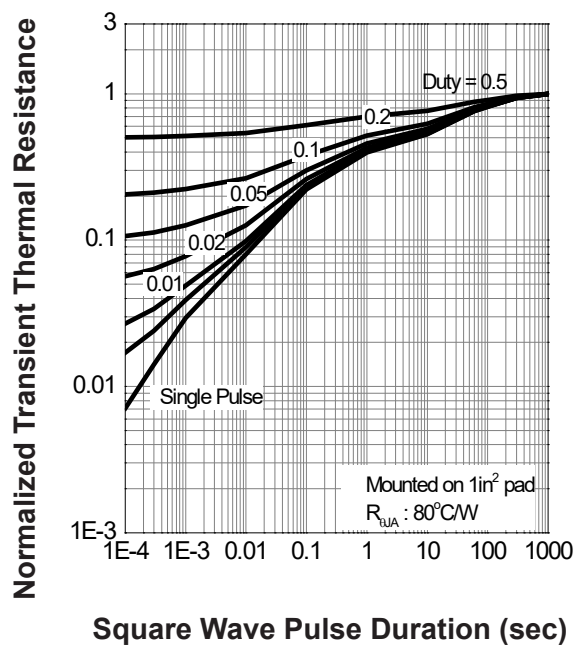


Channel 1 Typical Operating Characteristics(Cont.)

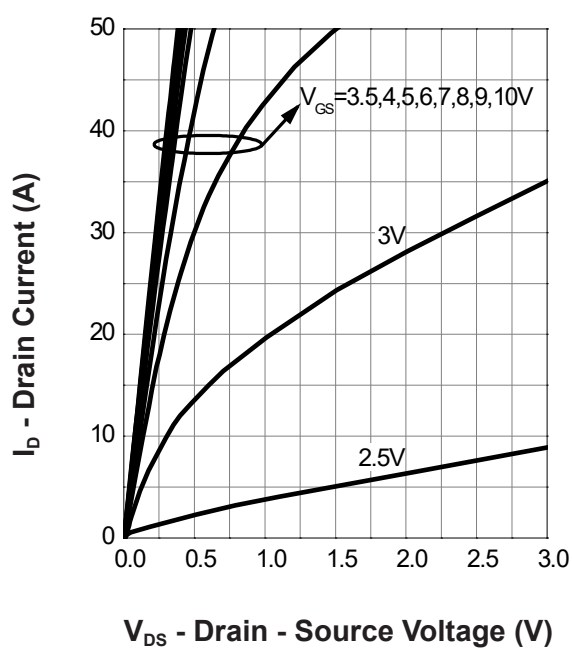
Safe Operation Area



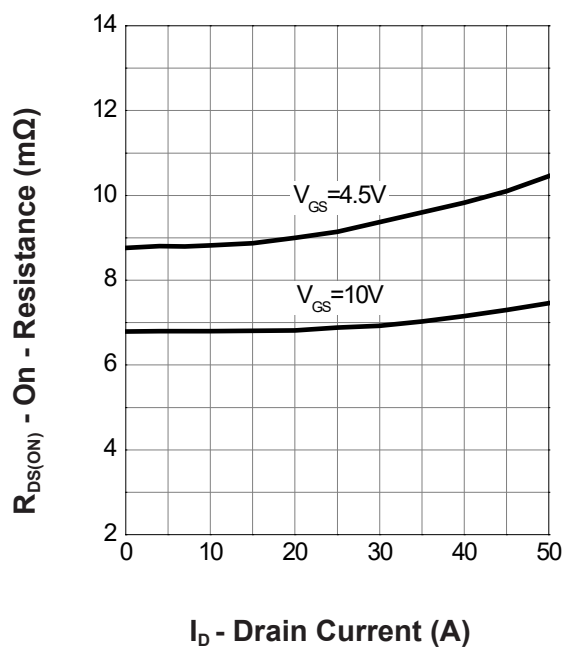
Thermal Transient Impedance



Output Characteristics

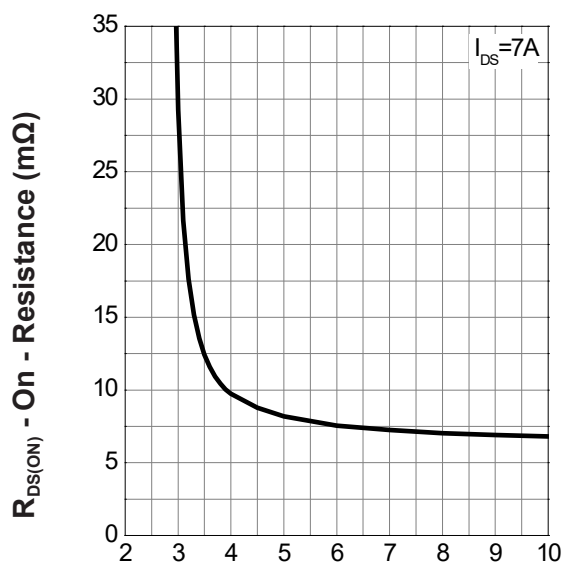


Drain-Source On Resistance

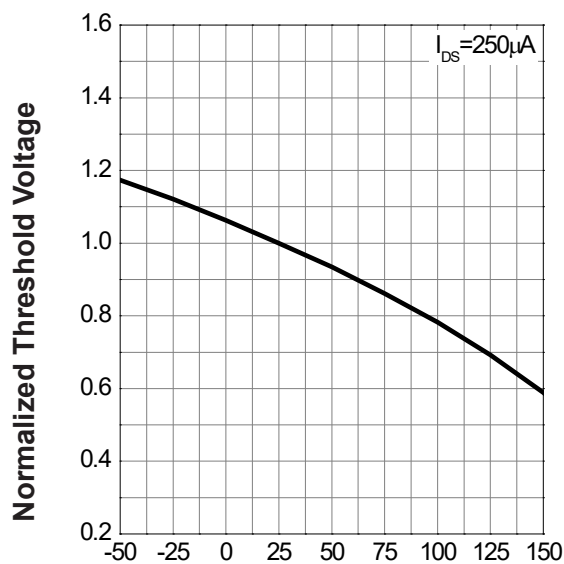


Channel 1 Typical Operating Characteristics(Cont.)

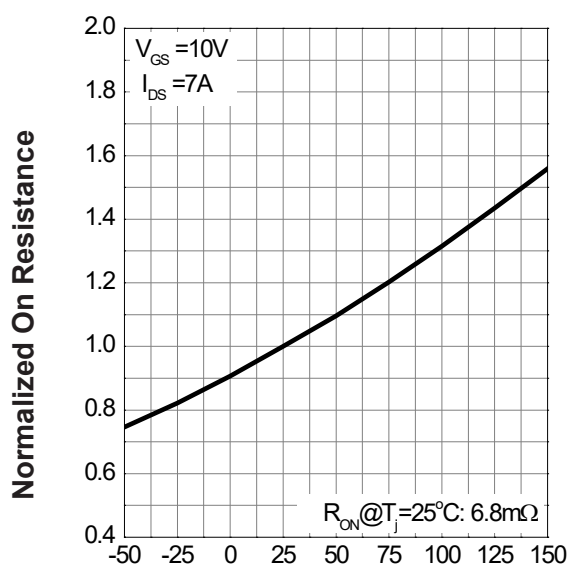
Gate-Source On Resistance

 V_{GS} - Gate - Source Voltage (V)

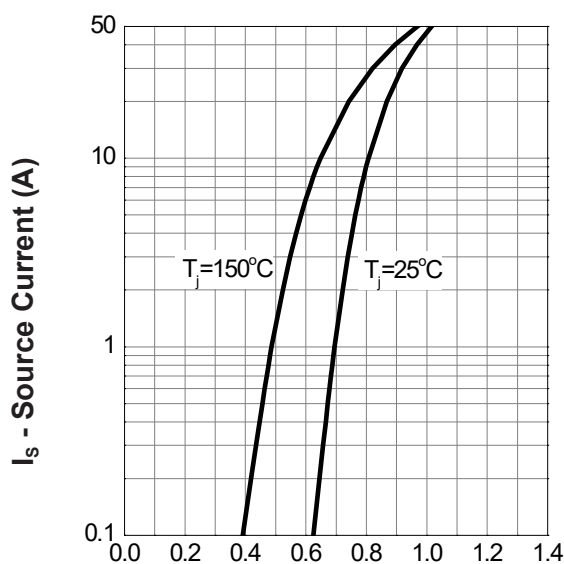
Gate Threshold Voltage

 T_J - Junction Temperature (°C)

Drain-Source On Resistance

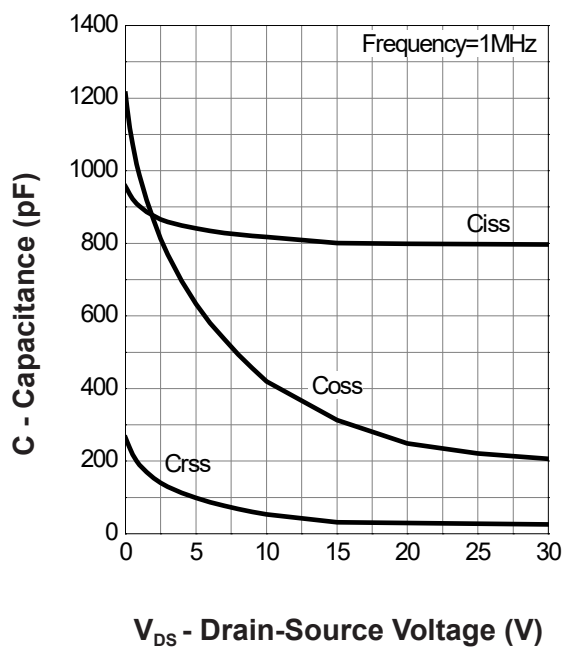
 T_J - Junction Temperature (°C)

Source-Drain Diode Forward

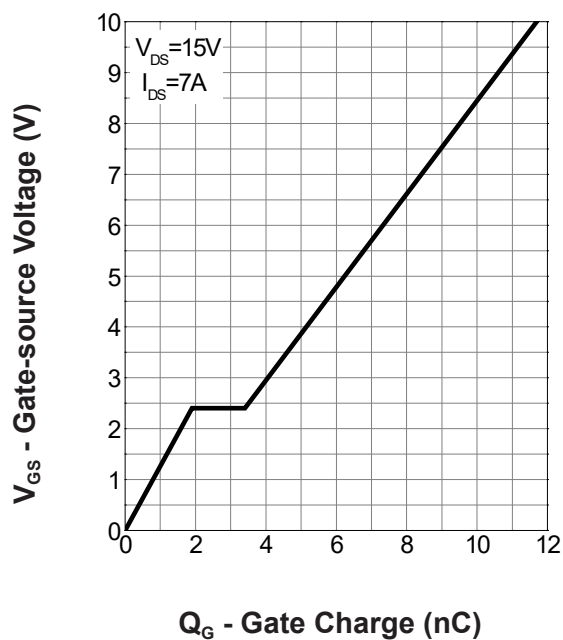
 V_{SD} - Source - Drain Voltage (V)

Channel 1 Typical Operating Characteristics(Cont.)

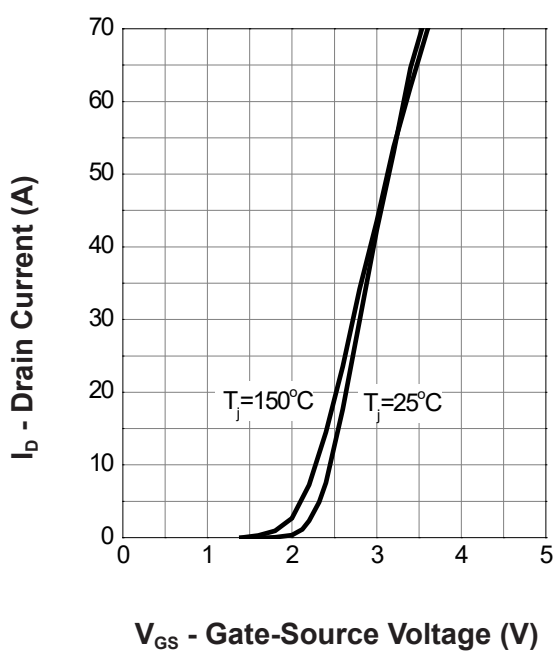
Capacitance



Gate Charge

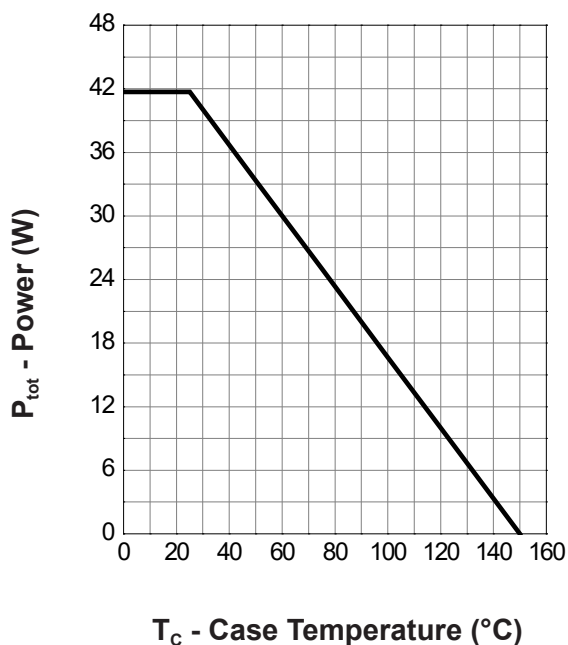


Transfer Characteristics

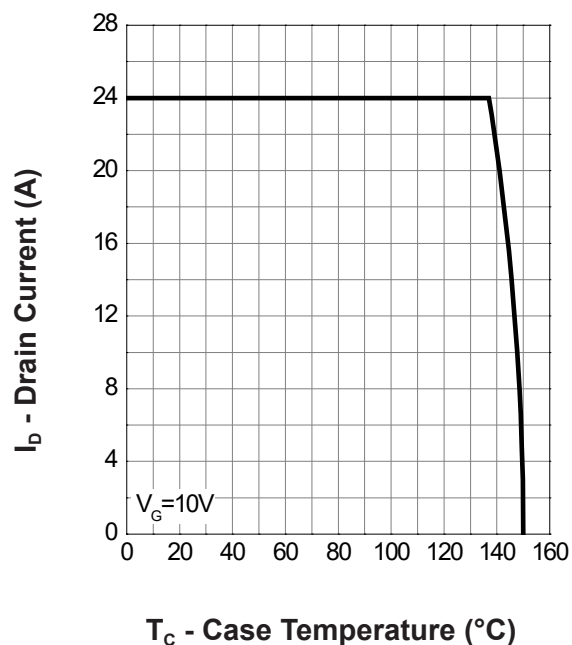


Channel 2 Typical Operating Characteristics

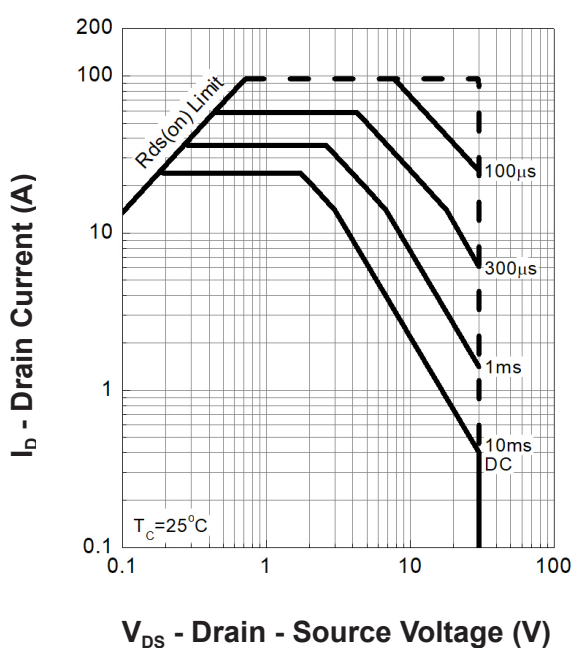
Power Dissipation



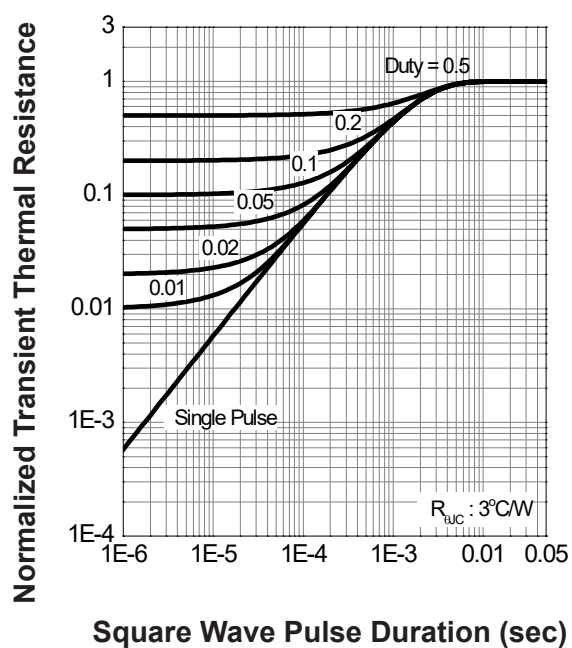
Drain Current



Safe Operation Area

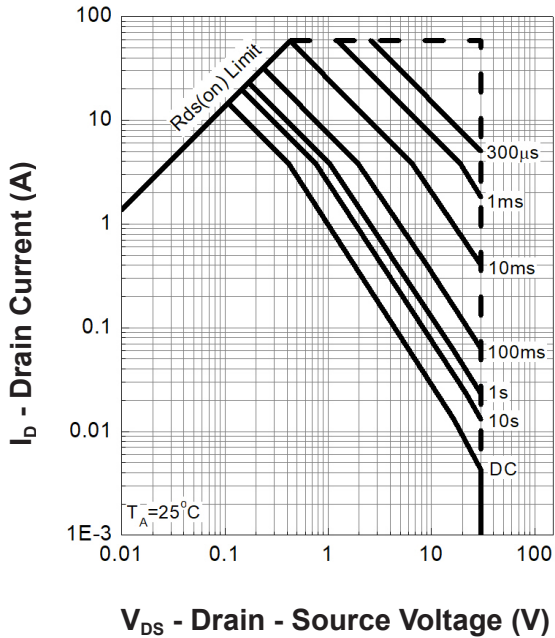


Thermal Transient Impedance

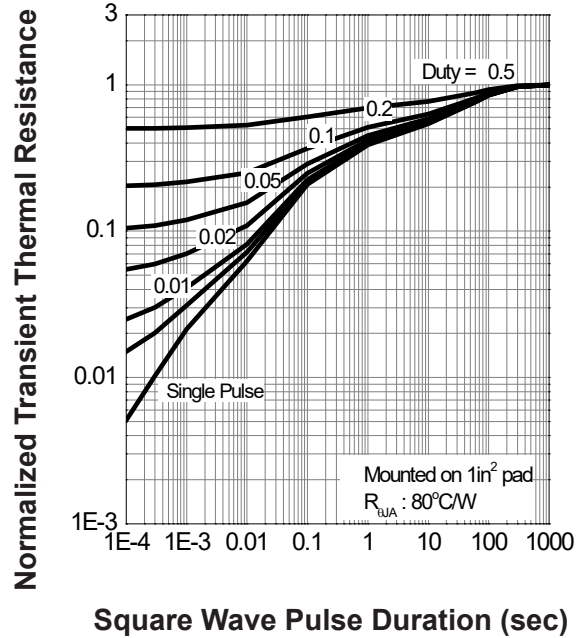


Channel 2 Typical Operating Characteristics(Cont.)

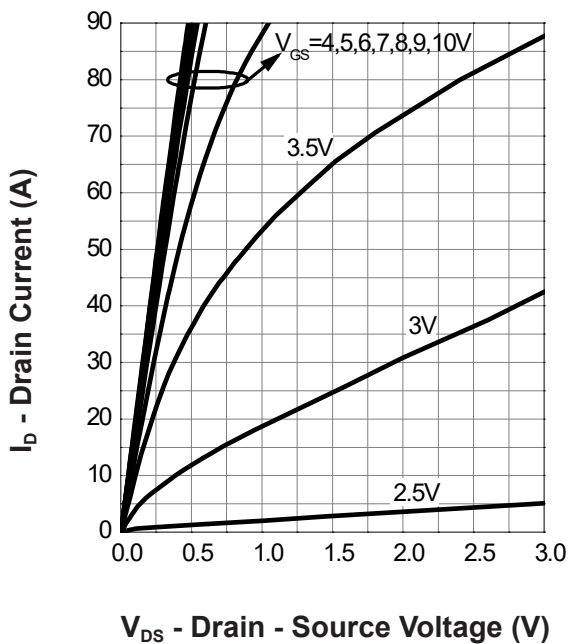
Safe Operation Area



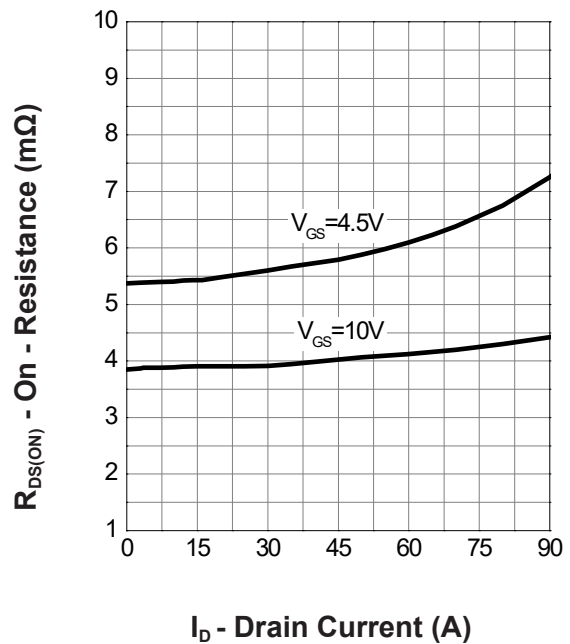
Thermal Transient Impedance



Output Characteristics

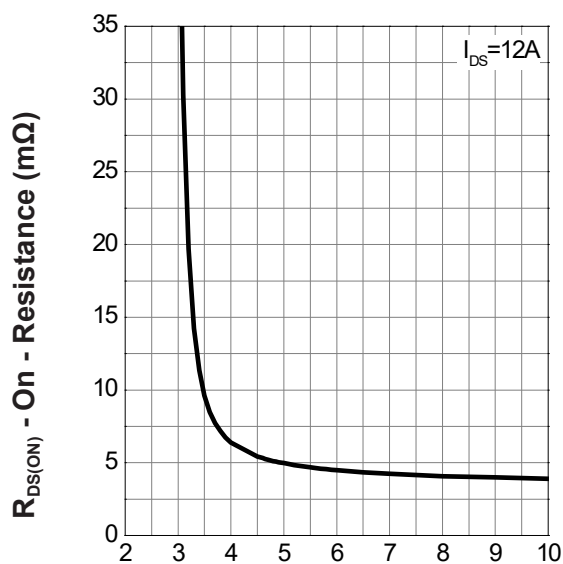


Drain-Source On Resistance

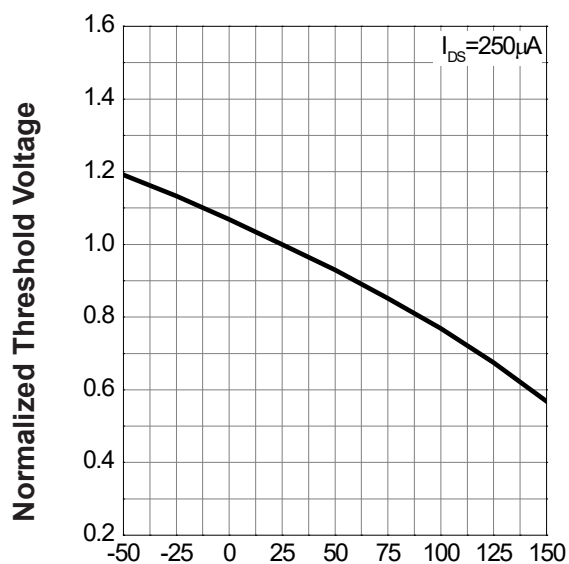


Channel 2 Typical Operating Characteristics(Cont.)

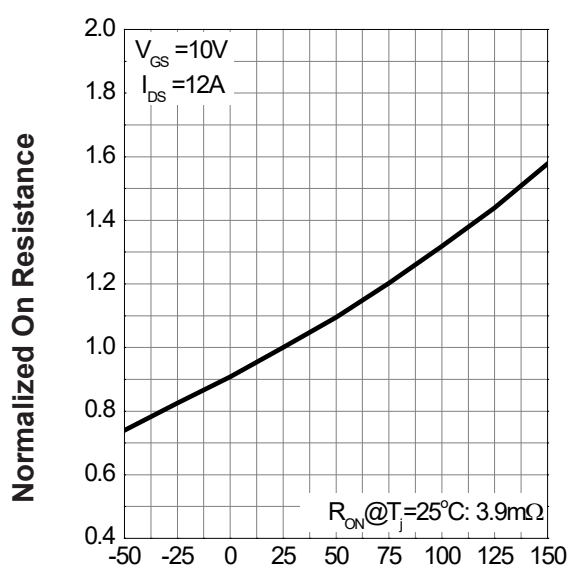
Gate-Source On Resistance

 V_{GS} - Gate - Source Voltage (V)

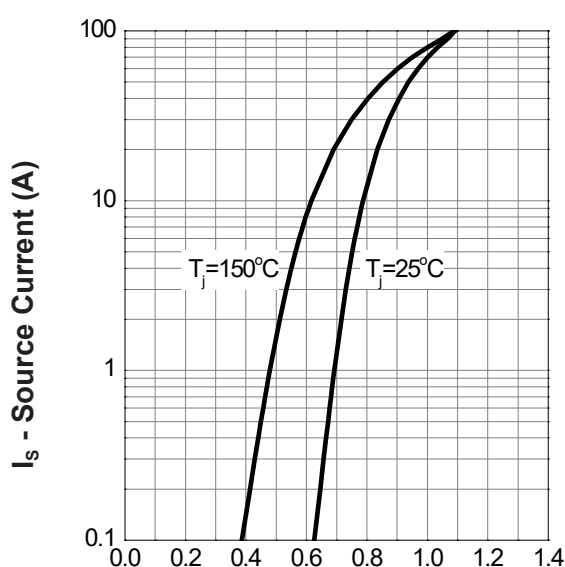
Gate Threshold Voltage

 T_J - Junction Temperature (°C)

Drain-Source On Resistance

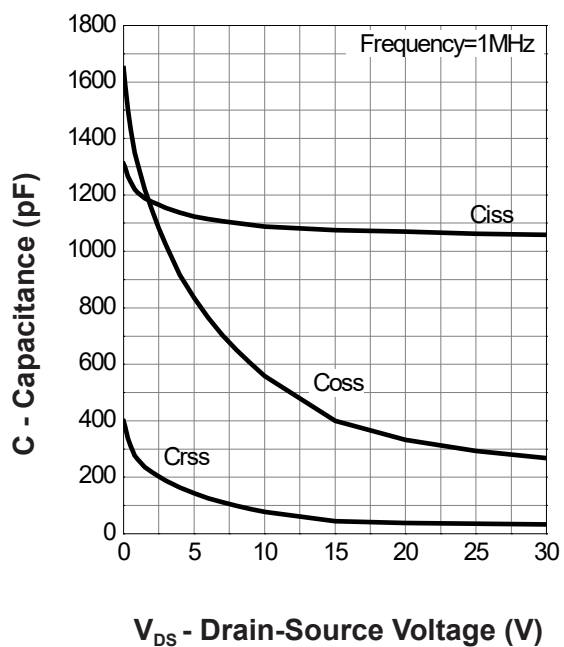
 T_J - Junction Temperature (°C)

Source-Drain Diode Forward

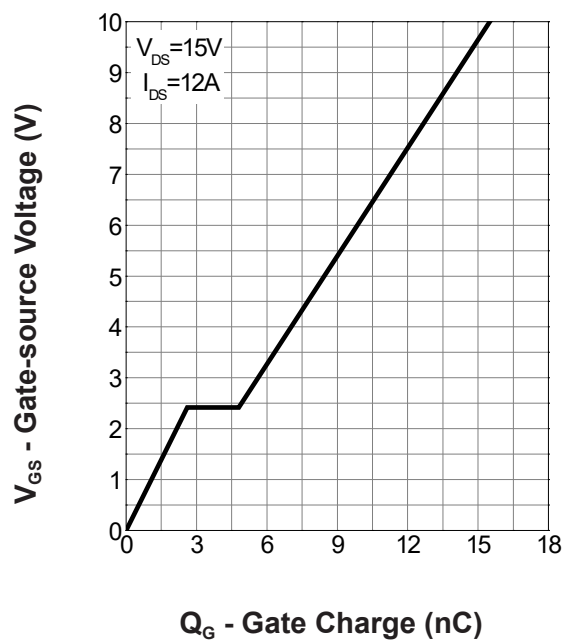
 V_{SD} - Source - Drain Voltage (V)

Channel 2 Typical Operating Characteristics(Cont.)

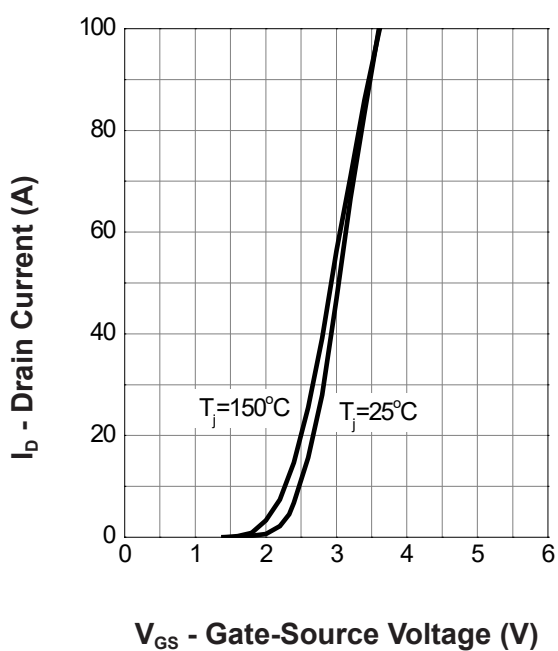
Capacitance



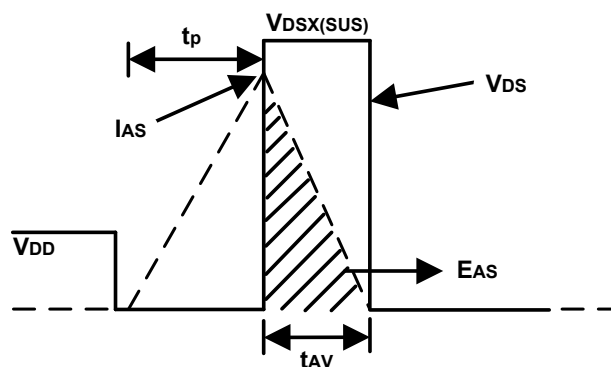
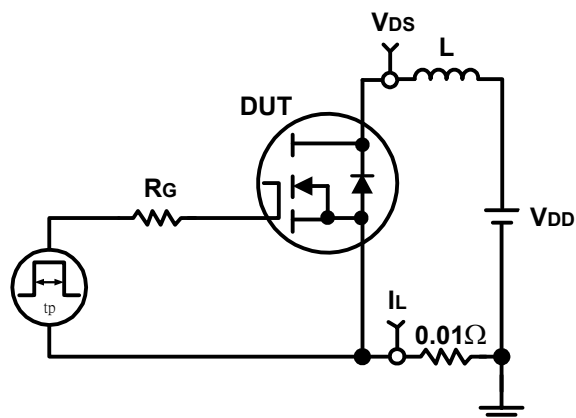
Gate Charge



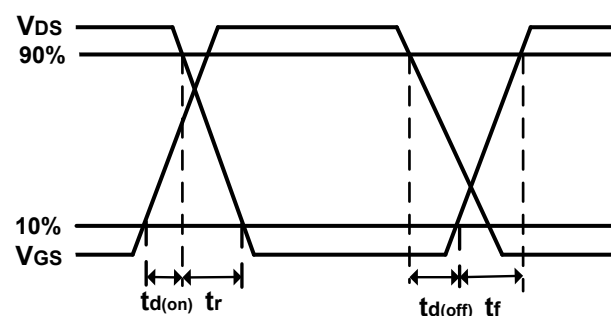
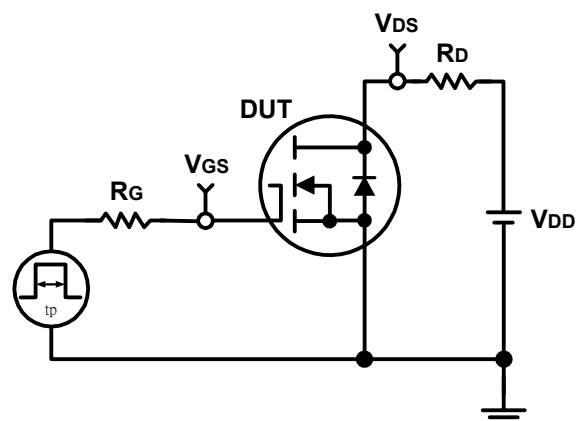
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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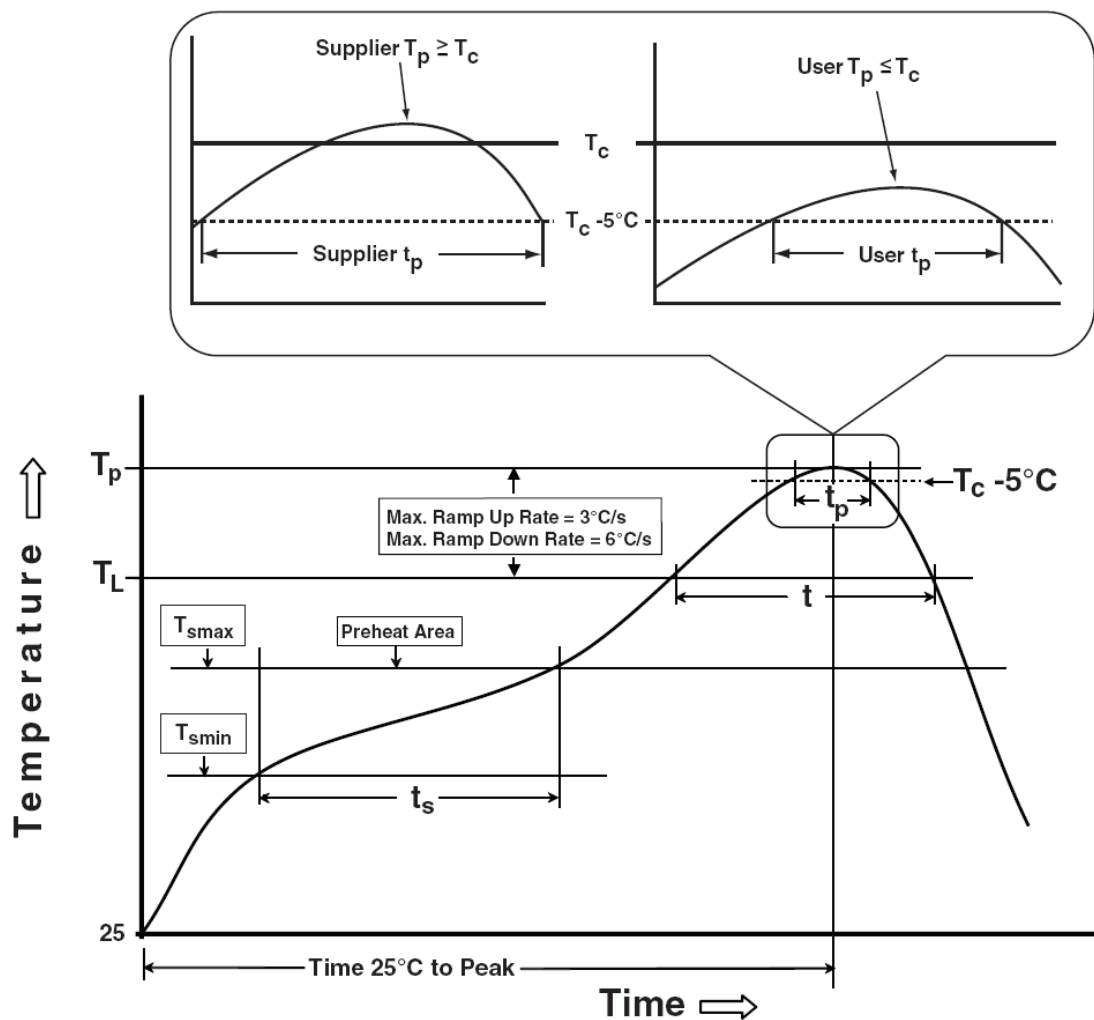
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In order to unify the quality and performance, Sinopower has been following JEDEC while defines assembly rule. Notwithstanding all the suppliers basically follow the rule for each product, different processes may cause slightly different results.

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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Customer Service

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